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DATE MAILED: 09/09/2004

APPLICATION NO.	FILING I	DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/034,228	12/28/2001		Woo Seock Cheong	CU-2757VE	9093
26530	7590	09/09/2004		EXAMINER	
LADAS & PARRY LLP			PHAM, LONG		
224 SOUTH MICHIGAN AVENUE SUITE 1200				ART UNIT	PAPER NUMBER
CHICAGO, IL 60604				2814	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)				
		10/034,228	CHEONG, WOO SEOCK	CHEONG, WOO SEOCK			
	Office Action Summary	Examiner	Art Unit				
		Long Pham	2814				
Period fo	The MAILING DATE of this communication or Reply	appears on the cover sheet	vith the correspondence address				
THE   - Exter after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR RE MAILING DATE OF THIS COMMUNICATIO sisions of time may be available under the provisions of 37 CFR SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a period for reply is specified above, the maximum statutory per re to reply within the set or extended period for reply will, by state ply received by the Office later than three months after the made patent term adjustment. See 37 CFR 1.704(b).	N. R 1.136(a). In no event, however, may a reply within the statutory minimum of the riod will apply and will expire SIX (6) MO atute, cause the application to become	a reply be timely filed  irty (30) days will be considered timely.  DNTHS from the mailing date of this communication.  ABANDONED (35 U.S.C. § 133).				
Status							
1)⊠	Responsive to communication(s) filed on 18	<u> 3 June 2004</u> .					
2a)⊠	This action is <b>FINAL</b> . 2b) T	his action is non-final.					
3)[	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Dispositi	on of Claims						
5)□ 6)⊠ 7)⊠	Claim(s) <u>1-48</u> is/are pending in the applicated 4a) Of the above claim(s) <u>6-9,13,16-24,26,2</u> Claim(s) is/are allowed. Claim(s) <u>1-3 and 10</u> is/are rejected. Claim(s) <u>4,5,11,12,14,15,25 and 28</u> is/are of Claim(s) are subject to restriction and	7 and 29-48 is/are withdrav	n from consideration.				
Applicati	on Papers						
9)□	The specification is objected to by the Exam	iner.					
10)	☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.						
	Applicant may not request that any objection to						
11)	Replacement drawing sheet(s) including the con The oath or declaration is objected to by the						
Priority ι	ınder 35 U.S.C. § 119						
a)[	Acknowledgment is made of a claim for fore  All b) Some * c) None of:  1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the papplication from the International Bursee the attached detailed Office action for a	ents have been received. ents have been received in priority documents have been reau (PCT Rule 17.2(a)).	Application No n received in this National Stage				
Attachmen	t(s)						
_	e of References Cited (PTO-892)	4) Interview	Summary (PTO-413)				
2)  Notic 3) Inform	e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449 or PTO/SB/ r No(s)/Mail Date	Paper No	o(s)/Mail Date Informal Patent Application (PTO-152)				

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#### **DETAILED ACTION**

Paper copies of cited U.S. patents and U.S. patent application publications will cease to be mailed to applicants with Office actions as of June 2004. Paper copies of foreign patents and non-patent literature will continue to be included with office actions. These cited U.S. patents and patent application publications are available for download via the Office's PAIR. As an alternate source, all U.S. patents and patent application publications are available on the USPTO web site (www.uspto.gov), from the Office of Public Records and from commercial sources. Applicants are referred to the Electronic Business Center (EBC) at <a href="http://www.uspto.gov/ebc/index.html">http://www.uspto.gov/ebc/index.html</a> or 1-866-217-9197 for information on this policy. Requests to restart a period for response due to a missing U.S. patent or patent application publications will not be granted.

### Response to Arguments

1. Applicant's arguments with respect to claims 1, 2, 3, and 10 have been considered but are most in view of the new ground(s) of rejection.

## Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claims 1, 2, 3, and 10 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kim (US 2001/0036730 A1) in combination of the applicant's admitted prior art (AAPA) of this application.

With respect to claim 1, Kim teaches a method of manufacturing a semiconductor device comprising the steps of (see figures 1A-1B and associated text):

forming an insulating layer 16 on a semiconductor substrate 10;

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forming a contact hole 19in the insulating layer;

forming a nitride layer 20 on the side of the contact hole; and forming a selective conductive plug 22 in the contact hole, including the nitride layer.

Kim does not appear to teach that the semiconductor substrate is made of silicon.

However, the use of silicon substrate is well-known to one skilled in the art of semiconductor device.

With respect to claim 2, Kim fails to teach the recited steps.

AAPA teaches a process comprising of: forming a gate structure 3 on a silicon substrate 1; forming an insulating layer spacer 5 on the gate structure; and forming an interlayer insulating layer 7 on the insulating layer spacer on the gate structure. See the Description of the Related Art and figures 1-4 of this application.

It would have been obvious to one of <u>ordinary skill</u> in the art of making semiconductor devices to incorporate the teachings of AAPA into Kim's process to reduce contact resistance. . See the Description of the Related Art and figures 1-4 of this application.

AAPA fails to teach that the interlayer insulating layer is made of oxide.

However, the use of oxide insulating layer is well-known in the art of making semiconductor device.

With respect to claim 3, AAPA further teaches forming the interlayer insulating layer on the whole structure, including the insulating spacer, and selectively removing the interlayer insulating layer so that only the insulating layer spacer on the gate structure remains. See the Description of the Related Art and figures 1-4 of this application.

AAPA fails to teach the removal of the interlayer insulating layer is done by wet etching.

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However, the removal of insulator by wet etching is well-known in the art of making semiconductor device.

With respect to claim 10, the use of oxide or nitride as spacer material is well-known in the art of making semiconductor device.

### Allowable Subject Matter

4. Claims 4, 5, 11, 12, 14, 15, 25, and 28 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Claims 18, 28, 29, and 30-48 which depend on claims of a non-elected species are withdrawn from examination.

#### Conclusion

5. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Long Pham whose telephone number is 571-272-1714. The examiner can normally be reached on M-F, 7:30AM-3:00PM.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on 571-272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Long Pham

Primary Examiner

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